

100V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	I _D T _C = +25°C
100V	$28m\Omega$ @ $V_{GS} = 10V$	40A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Power Management Functions
- DC-DC Converters

Features

- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile Ideal for Thin Applications
- Lead-Free Finish; RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMNH10H028SPSQ)

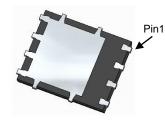
Mechanical Data

- Case: POWERDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.097 grams (Approximate)

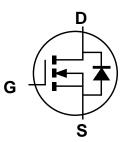




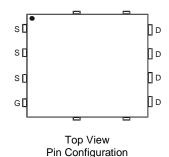
Top View



Bottom View



Internal Schematic



Ordering Information (Note 4)

Part Number	Case	Packaging
DMNH10H028SPS-13	POWERDI [®] 5060-8	2500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Dil=Manufacturer's Marking
H1H28SS = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 15 = 2015)
WW = Week Code (01 to 53)

POWERDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@ $T_C = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	100	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I _D	40 25	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) (Note 5)			I _{DM}	54	Α
Maximum Continuous Body Diode Forward Current (Note 6)			Is	3.9	Α
Avalanche Current (Note 8) L=0.1mH			I _{AS}	26	Α
Avalanche Energy (Note 8) L=0.1mH			E _{AS}	35	mJ

Thermal Characteristics

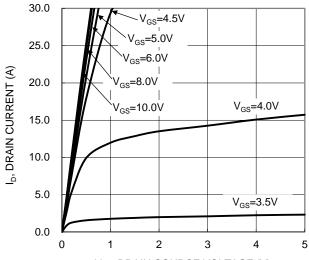
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P_{D}	1.6	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{\theta JA}$	97	°C/W
Total Power Dissipation (Note 6)		P _D	2.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{\theta JA}$	52	°C/W
Thermal Resistance, Junction to Case		$R_{\theta JC}$	1.8	C/VV
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@ $T_C = +25$ °C, unless otherwise specified.)

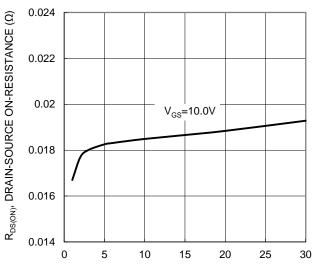
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}		_	1.0	μΑ	$V_{DS} = 100V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	2.0	2.5	4.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
Static Drain-Source On-Resistance	R _{DS(ON)}		19	28	mΩ	$V_{GS} = 10V, I_D = 20A$
Diode Forward Voltage	V_{SD}		0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1.0A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	2245	_		$V_{DS} = 50V, V_{GS} = 0V$ f = 1.0MHz
Output Capacitance	Coss		173	_	pF	
Reverse Transfer Capacitance	C _{rss}	_	68	_		
Gate Resistance	R _G		1.9	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V _{GS} = 10V)	Q_g		36	_		
Total Gate Charge (V _{GS} = 6.0V)	Qg	_	22	_	nC	$V_{DD} = 50V, I_D = 20A$
Gate-Source Charge	Q_{gs}		7.3	_	110	
Gate-Drain Charge	Q_{gd}	_	9.2	_		
Turn-On Delay Time	t _{D(ON)}		6.4	_		V _{GS} = 10V, V _{DS} = 50V,
Turn-On Rise Time	t _R	-	5.8	_	20	
Turn-Off Delay Time	t _{D(OFF)}	_	17.8	_	ns	$R_G = 3.0\Omega$, $I_D = 20A$
Turn-Off Fall Time	t _F	_	4.8	_		
Reverse Recovery Time	t _{RR}	_	35	_	ns	$I_F = 20A$, $di/dt = 100A/\mu s$
Reverse Recovery Charge	Q _{RR}	_	47	_	nC	$I_F = 20A$, $di/dt = 100A/\mu s$

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing. Notes:





V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 1. Typical Output Characteristic



I_D, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-resistance vs. Drain Current and Gate Voltage

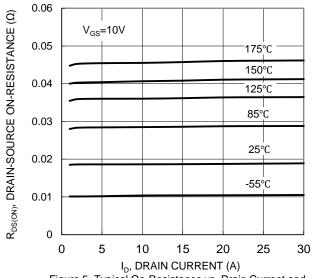
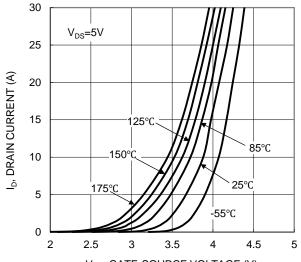
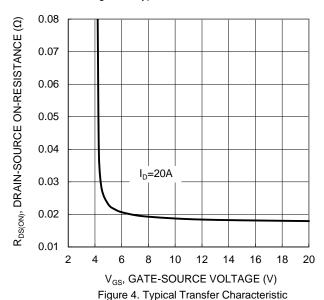


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic



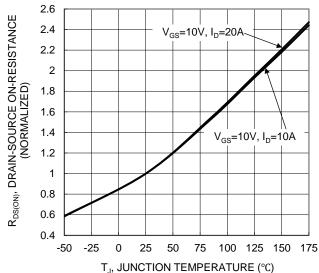


Figure 6. On-Resistance Variation with Temperature



DMNH10H028SPS

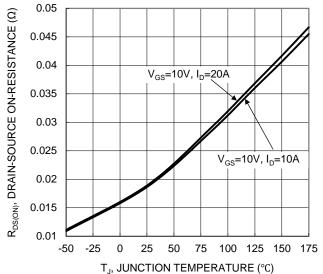
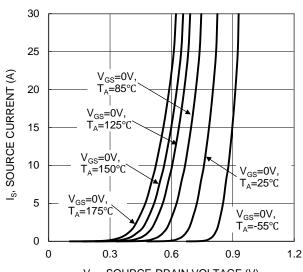
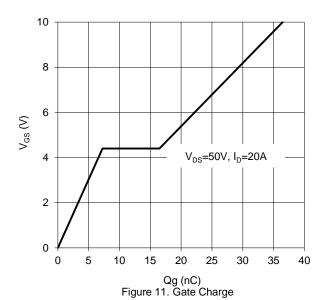


Figure 7. On-Resistance Variation with Temperature

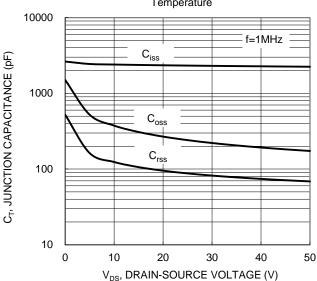


V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current



3.2 $V_{GS(TH)}$, GATE THRESHOLD VOLTAGE (V) 3 2.8 2.6 2.4 $I_D=1mA$ 2.2 2 $I_{D} = 250 \mu A$ 1.8 1.6 1.4 1.2 -25 -50 0 25 50 75 100 125 150

T_J, JUNCTION TEMPERATURE (°C) Figure 8. Gate Threshold Variation vs. Junction Temperature



100 $R_{DS(ON)}$ Limited ID, DRAIN CURRENT (A) 10 T_{J(Max)}=175℃ T_{C} =25 $^{\circ}$ C 0.1 Single Pulse DUT on 1*MRP board V_{GS}=10V 0.01 0.1 1 10 100 1000 V_{DS}, DRAIN-SOURCE VOLTAGE (V)

Figure 12. SOA, Safe Operation Area

Figure 10. Typical Junction Capacitance



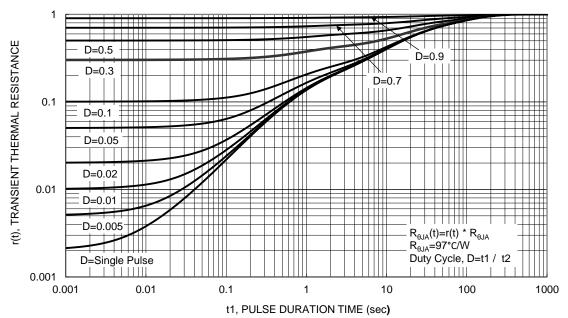
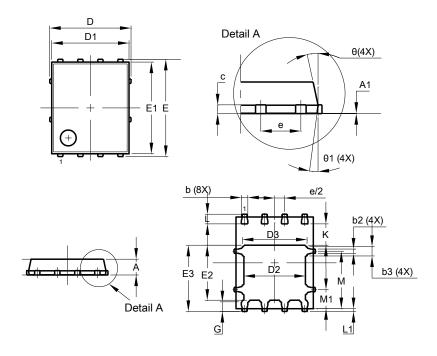


Figure 13. Transient Thermal Resistance



Package Outline Dimensions

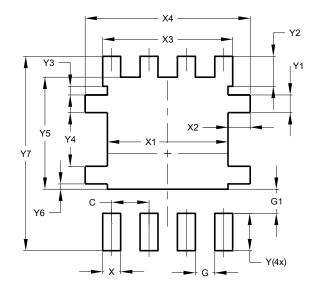
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



POWERDI®5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05			
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D	,	5.15 BSC	;		
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е		6.15 BSC	;		
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51				
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
M	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12º	11º		
Θ1	6°	80	7º		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
Х	0.610			
X1	4.100			
X2	0.755			
Х3	4.420			
X4	5.610			
Υ	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			



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